IHSS12A010T2

1200 V, 10 A, Silicon Carbide Schottky Diode

V_{RRM}	**1200 V**
I_F	**10 A**



TO-247-2

Features

- Zero reverse-recovery current
- Switching behaviour independent of temperature
- Positive temperature coefficient of V_F for easy paralleling

Typical applications

- Boost and totem-pole PFC
- EV charger and server power supplies
- Solar boost stages
- Freewheeling diode for SiC and IGBT switches

Description

1200 V, 10 A silicon-carbide Schottky diode, TO-247-2 package. Zero reverse-recovery charge for fast, low-loss switching.

Key specifications

Parameter	Value
V_{RRM}	1200 V
I_F, T_C = 140 °C	10 A
Configuration	Single
Reverse recovery	None (majority-carrier Schottky)

Full characterization data

Thermal resistance, forward voltage, capacitive charge, capacitance and typical characteristic curves for IHSS12A010T2 are available on request: request the full data or write to sales@ironhawksemi.com.

Package

TO-247-2. Mechanical outline drawing, STEP model and PCB footprint available on request.

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Ordering information

Part number	Packing	MOQ	Lead time
IHSS12A010T2	Tube	On request	On request

Information in this document is believed to be accurate but is subject to change without notice. Typical values are not guaranteed. The customer is responsible for validating suitability in the end application. IRONHAWK · sales@ironhawksemi.com

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